

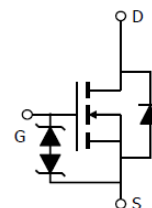
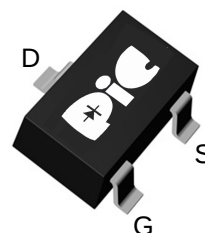
➤ General Description

This PAN6330ER N-Channel enhancement mode power field effect transistor is the high density trench technology and this advanced technology can provide excellent $R_{DS(ON)}$ performance and efficiency for power switching and load switching application., this device also comply with the RoHS and Green Product requirement with full function reliability approved.

➤ Feature

- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- ESD Protection (2KV) Diode design-in
- SOT-323 package design

➤ SOT-323



➤ Application

- Drivers: Relays, Solenoids, Lamps, Hammers, Display, Memories, Transistors, etc.
- High saturation current capability. Direct Logic-Level Interface: TTL/CMOS
- Battery Operated Systems
- Solid-State Relays

➤ Absolute Maximum Ratings

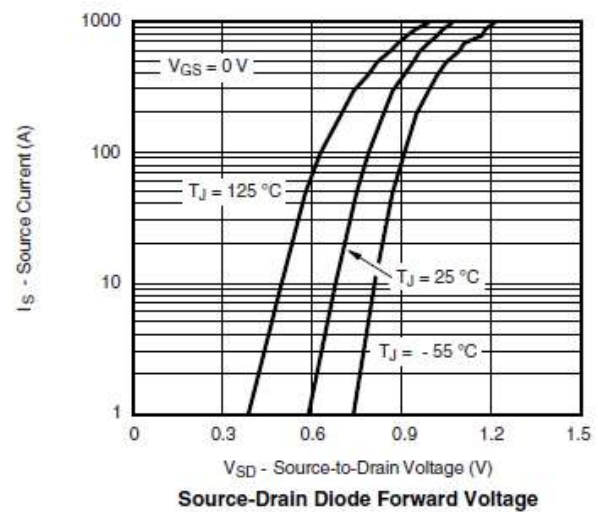
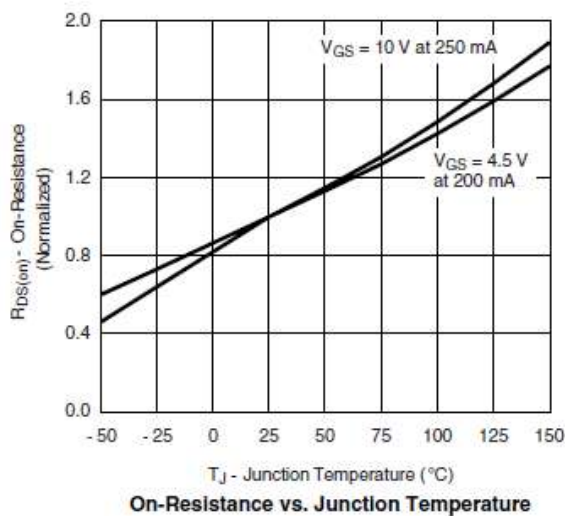
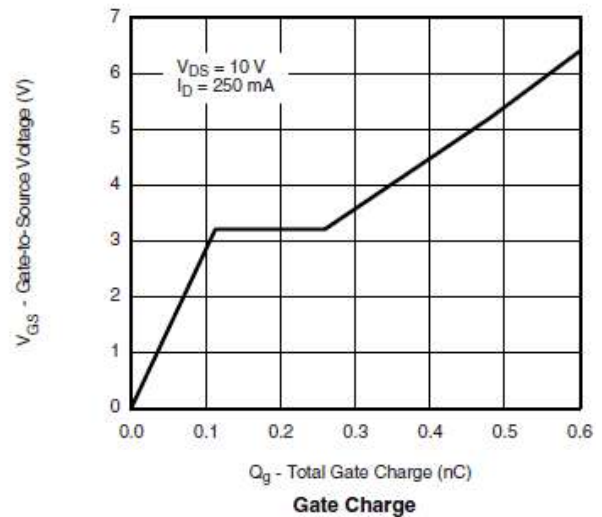
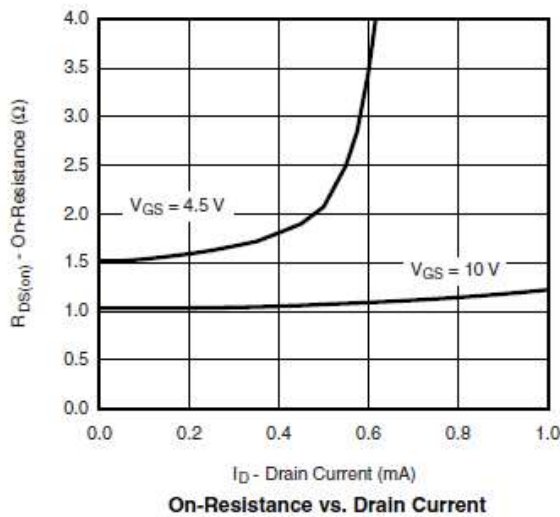
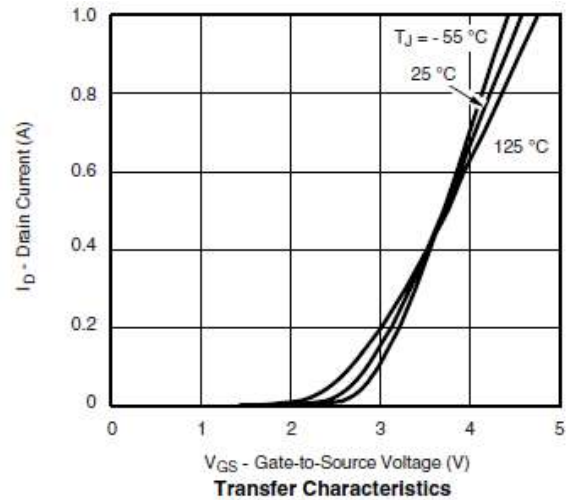
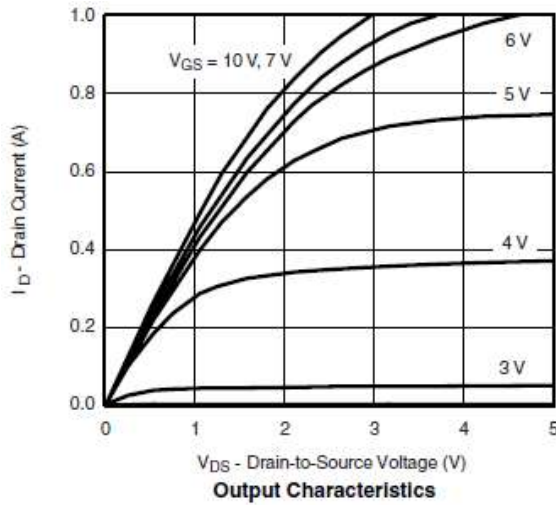
Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	60	V
Gate –Source Voltage	V_{GSS}	± 20	V
Continuous Drain Current($T_J=150^\circ C$)	I_D	$T_A=25^\circ C$ 0.5	A
		$T_A=70^\circ C$ 0.3	
Pulsed Drain Current	I_{DM}	1.0	A
Continuous Source Current(Diode Conduction)	I_S	0.4	A
Power Dissipation	P_D	$T_A=25^\circ C$ 0.35	W
		$T_A=70^\circ C$ 0.22	
Operating Junction Temperature	T_J	150	150
Storage Temperature Range	T_{STG}	-55/150	-55/150
Thermal Resistance-Junction to Ambient	$R_{\theta JA}$	120	120

➤ Electrical Characteristics ($T_A=25^\circ C$ Unless otherwise noted)

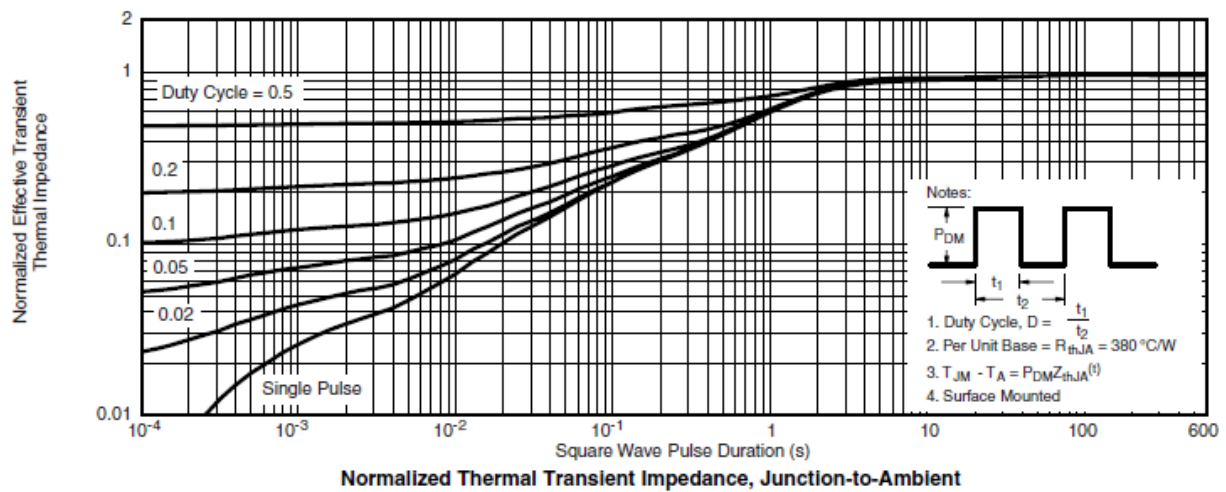
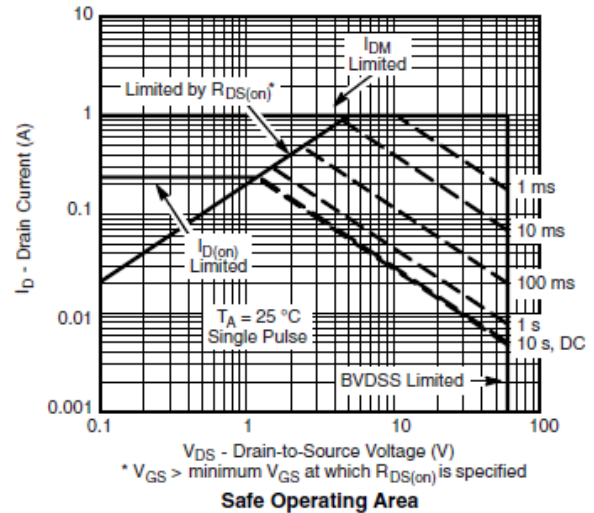
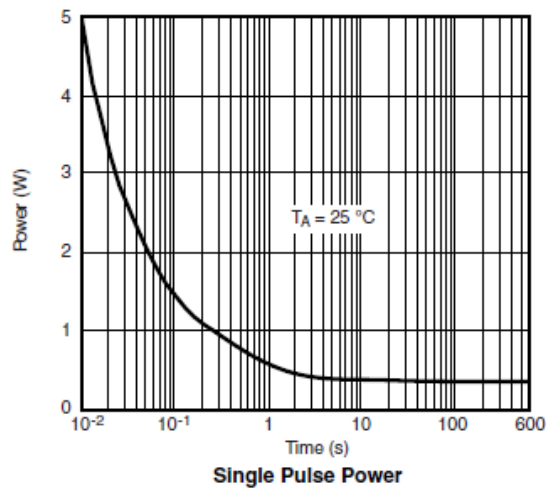
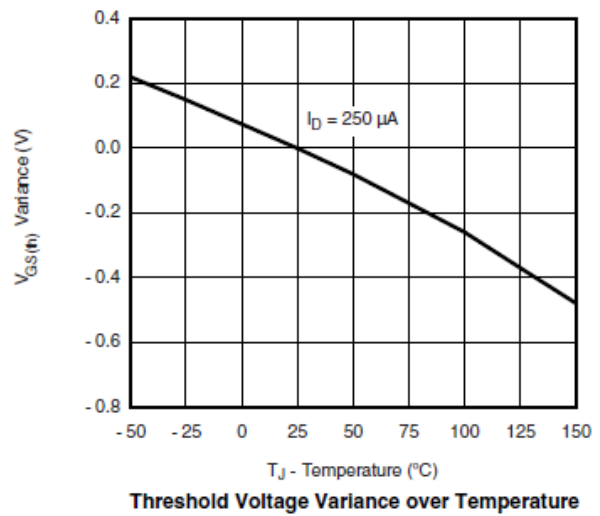
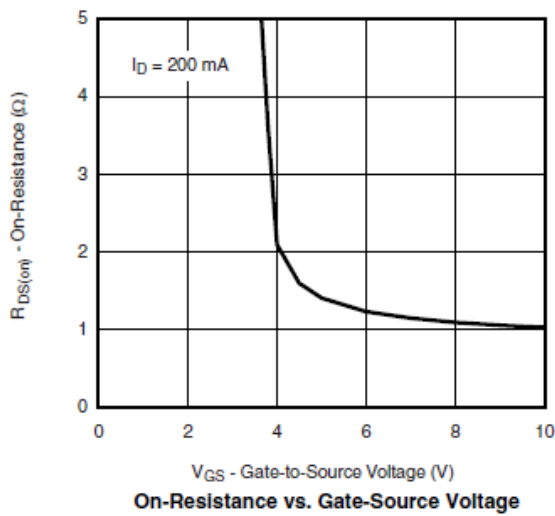
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	60			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0		2.0	
Gate Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$			3	μA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=60V, V_{GS}=0V$			1	μA
		$V_{DS}=60V, V_{GS}=0V$ $T_J=85^\circ C$			10	
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=0.5A$		1200	2400	$m\Omega$
		$V_{GS}=4.5V, I_D=0.3A$		1600	3000	
Forward Transconductance	g_{FS}	$V_{DS}=10V, I_D=0.2A$		0.2		S
Diode Forward Voltage	V_{SD}	$I_S=0.2A, V_{GS}=0V$		0.75	1.4	V
Dynamic						
Total Gate Charge	Q_g	$V_{DS}=10V, V_{GS}=4.5V$ $I_D \approx 0.25A$		450		pC
Gate-Source Charge	Q_{gs}			110		
Gate-Drain Charge	Q_{gd}			150		
Input Capacitance	C_{iss}	$V_{DS}=25V, V_{GS}=0V$ $f=1MHz$		30		pF
Output Capacitance	C_{oss}			8		
Reverse Transfer Capacitance	C_{rss}			5		
Turn-On Time	$t_{d(on)}$	$V_{DD}=30V, R_L=150\Omega$ $I_D \approx 0.2A, V_{GEN}=10V$ $R_G=10\Omega$		4	10	ns
	t_r			5	15	
Turn-Off Time	$t_{d(off)}$			12	20	
	t_f			10	20	

N-Ch 60V Fast Switching MOSFET
 $V_{DS}=60V$, $I_D=0.5A$, $R_{DS(on)}=2400m\Omega$

➤ Typical Characteristics



N-Ch 60V Fast Switching MOSFET
 $V_{DS}=60V$, $I_D=0.5A$, $R_{DS(on)}=2400m\Omega$



➤ Recommand IR Reflow Soldering Thermal Profile

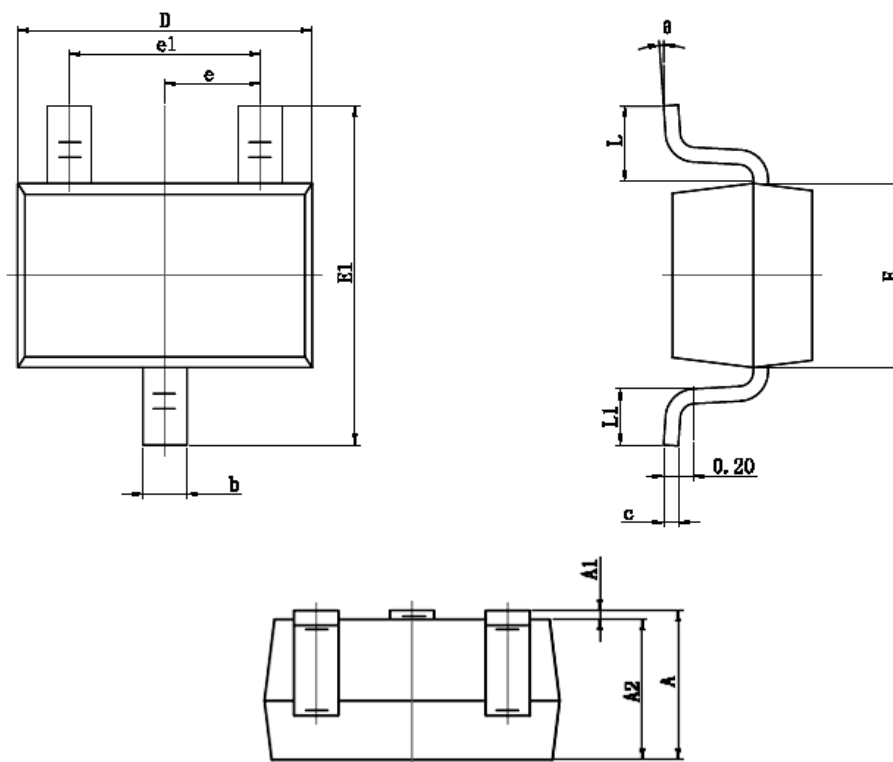


Profile Feature	Pb-Free Assembly Profile
Temperature Min. (T_{Smin})	150°C
Temperature Max. (T_{Smax})	200°C
Time (t_S) from (T_{Smin} to T_{Smax})	60-120 seconds
Average Ramp-up Rate (t_L to t_P)	3°C/second max.
Liquidous Temperature (T_L)	217°C
Time (t_L) Maintained Above (T_L)	60 – 150 seconds
Peak Temperature	260°C +0°C / -5°C
Time (t_P) within 5°C of actual Peak Temperature	30 seconds
Ramp-down Rate (T_P to T_L)	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.

➤ Ordering Information

Part Number	Description	Quantity
PAN6330ER	SOT-323 Reel	3000 pcs

➤ Package Information (SOT-323)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

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